

APM3195PU

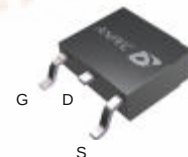


P-Channel Enhancement Mode MOSFET

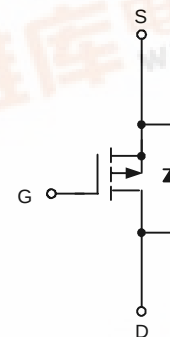
Features

- -30V/-11.8A ,
 $R_{DS(ON)} = 100m\Omega$ (typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 170m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

Pin Description



Top View of TO-252



P-Channel MOSFET

Applications

- Power Management in Desktop Computer or DC/DC Converters

Ordering and Marking Information

APM3195P □□-□□□ Lead Free Code Handling Code Temp. Range Package Code	Package Code U : TO-252 Operating Junction Temp. Range C : -55 to 150 °C Handling Code TU : Tube TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM3195P U : APM3195P XXXXX	XXXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds and 100% matte tin plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A = 25^\circ\text{C}$)			
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ -8	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ -20	A
		$T_C=100^\circ\text{C}$ -15	
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ -11.8	A
		$T_C=100^\circ\text{C}$ -7.5	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 50	W
		$T_C=100^\circ\text{C}$ 20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.5	$^\circ\text{C/W}$
Mounted on PCB of 1in² Pad Area			
I_{DP}	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ -20	A
		$T_A=100^\circ\text{C}$ -15	
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$ -3	A
		$T_A=100^\circ\text{C}$ -2	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 2.5	W
		$T_A=100^\circ\text{C}$ 1	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	50	$^\circ\text{C/W}$
Mounted on PCB of Minimum Footprint			
I_{DP}	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ -50	A
		$T_A=100^\circ\text{C}$ -30	
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$ -2	A
		$T_A=100^\circ\text{C}$ -1	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 1.6	W
		$T_A=100^\circ\text{C}$ 0.6	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	75	$^\circ\text{C/W}$

Electrical Characteristics (T_A = 25°C unless otherwise noted)

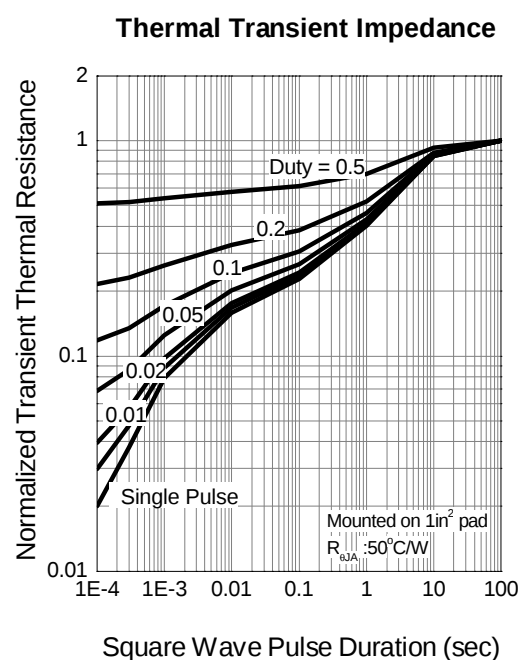
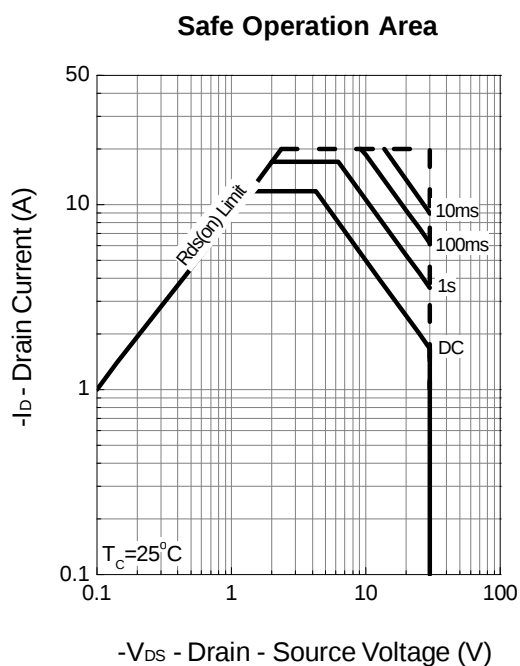
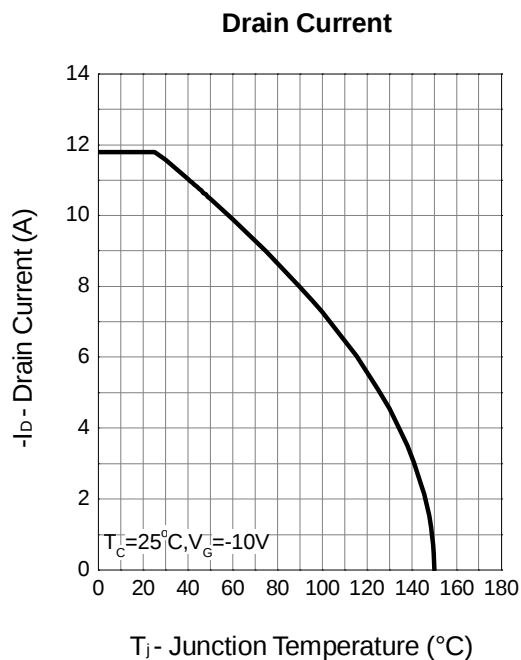
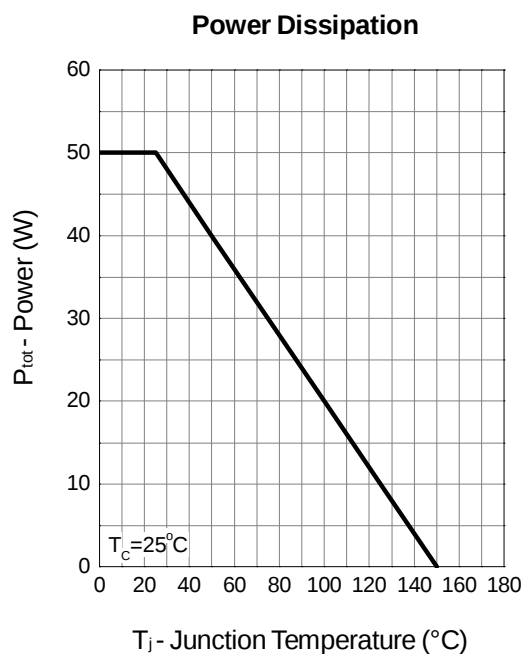
Symbol	Parameter	Test Condition	APM3195PU			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V			-1	μA
		T _J =85°C			-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1	-1.5	-2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-4A		100	240	mΩ
		V _{GS} =-4.5V, I _{DS} =-3A		170	460	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-0.5A, V _{GS} =0V		-0.8	-1.3	V
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		11		Ω
C _{iSS}	Input Capacitance	V _{GS} =0V V _{DS} =-25V Frequency=1.0MHz		510		pF
C _{oss}	Output Capacitance			70		
C _{rSS}	Reverse Transfer Capacitance			36		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =15Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω		10	20	ns
T _r	Turn-on Rise Time			8	20	
t _{d(OFF)}	Turn-off Delay Time			25	50	
T _f	Turn-off Fall Time			5	15	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _{DS} =-4A		8.1	10.5	nC
Q _{gs}	Gate-Source Charge			2		
Q _{gd}	Gate-Drain Charge			1.1		

Notes:

a : Pulse test ; pulse width≤300μs, duty cycle≤2%.

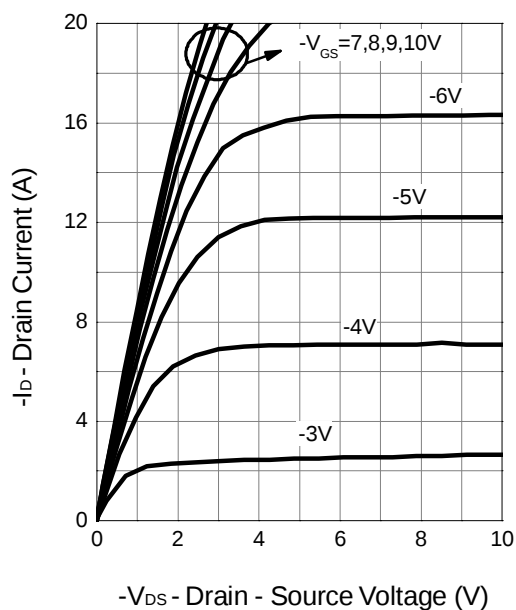
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

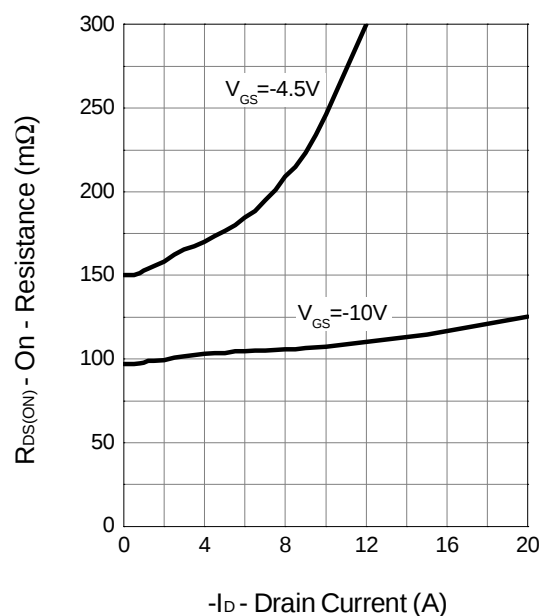


Typical Characteristics (Cont.)

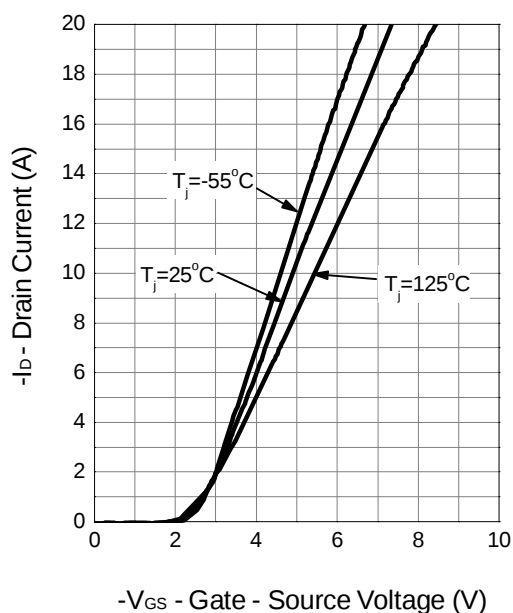
Output Characteristics



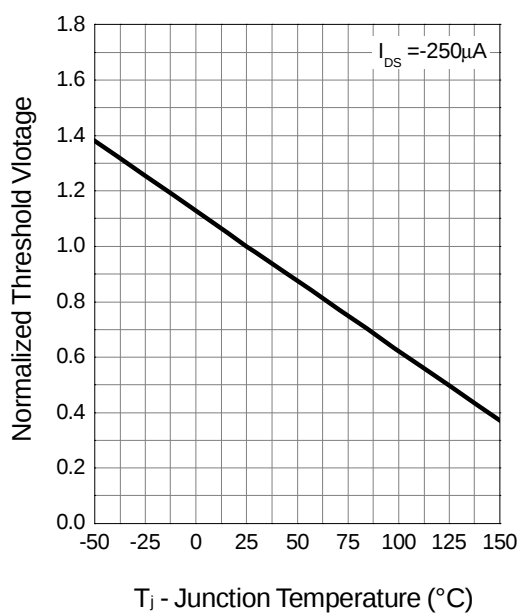
Drain-Source On Resistance



Transfer Characteristics

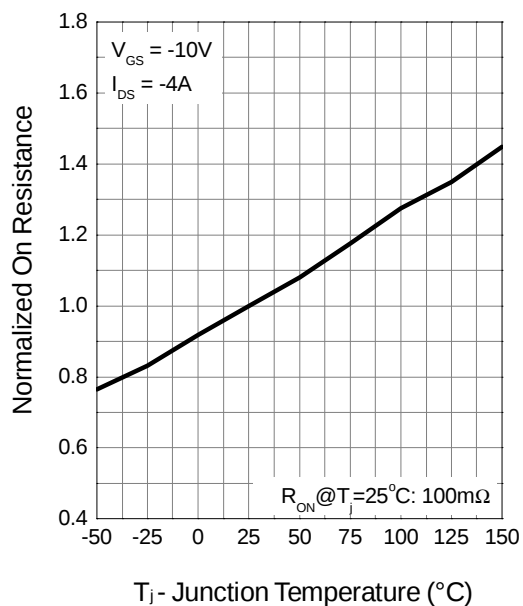


Gate Threshold Voltage

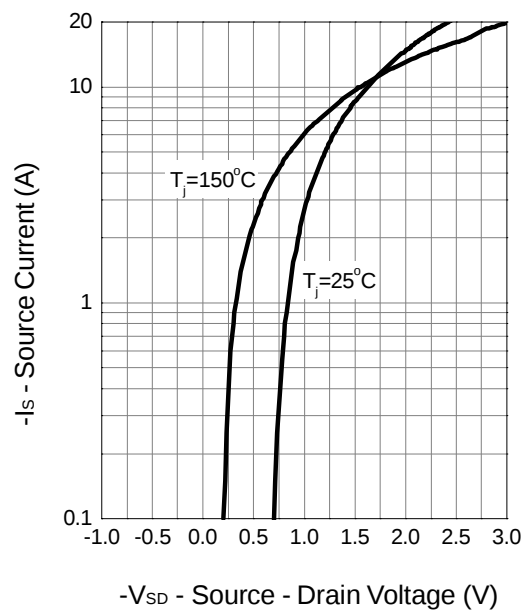


Typical Characteristics (Cont.)

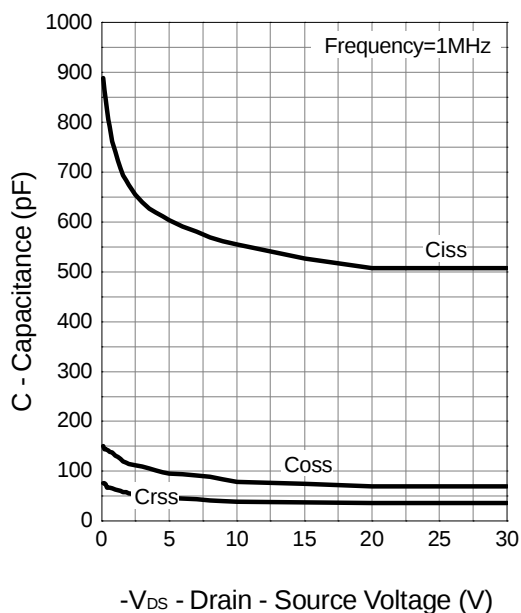
Drain-Source On Resistance



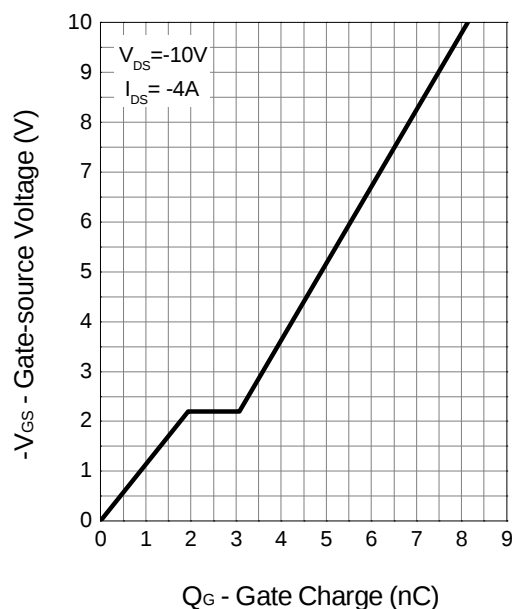
Source-Drain Diode Forward



Capacitance

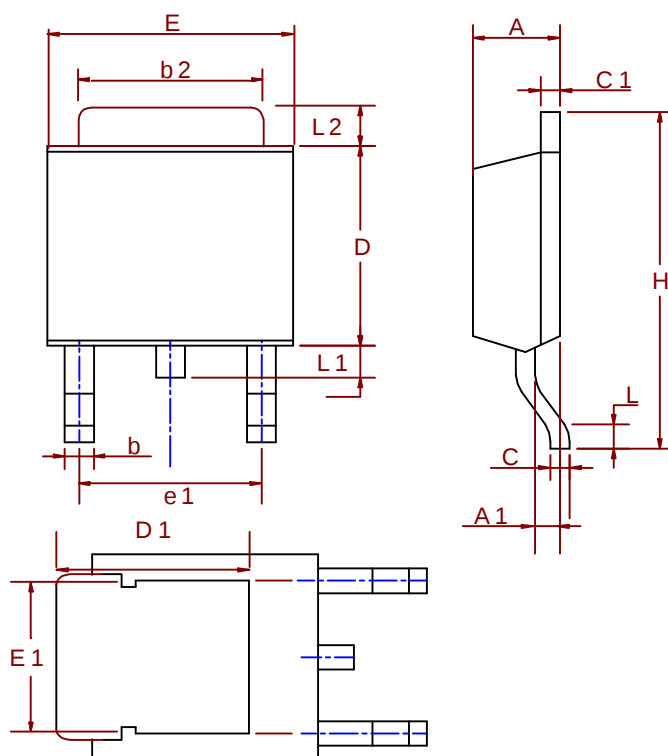


Gate Charge



Package Information

TO-252 (Reference JEDEC Registration TO-252)

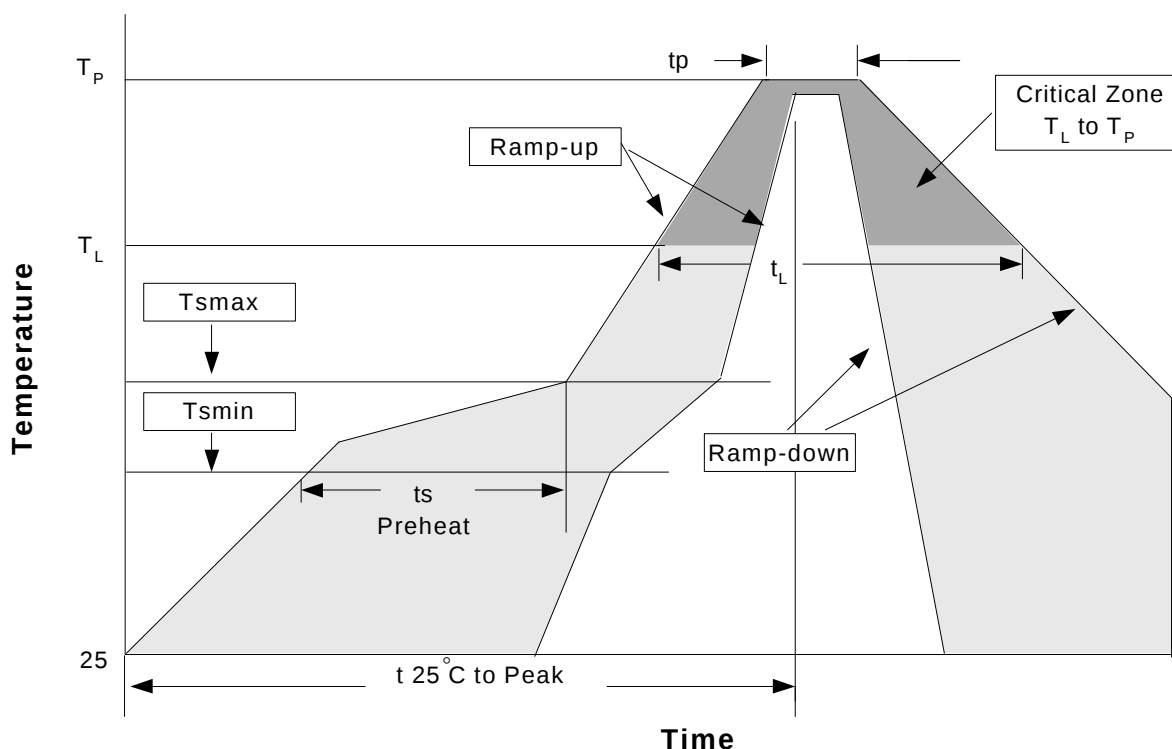


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
D1	5.2 REF		0.205 REF	
E	6.35	6.73	0.250	0.265
E1	5.3 REF		0.209 REF	
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T _p)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t _p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

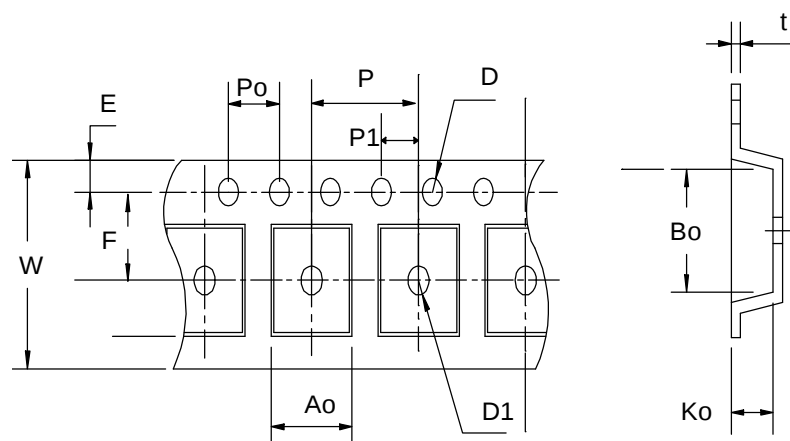
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

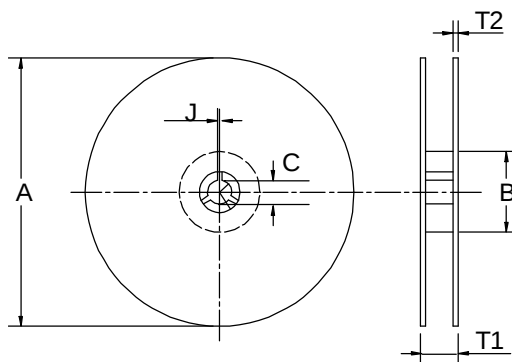
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions (Cont.)



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ±3	100 ± 2	13 ± 0.5	2 ± 0.5	16.4 +0.3 -0.2	2.5± 0.5	16+ 0.3 - 0.1	8 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ± 0.1	1.5 +0.1	1.5± 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4± 0.1	2.5± 0.1	0.3±0.05

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

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